

XP-002226511

AN - 2002-009107 [01]
AP - TW20000100143 20000106

CPY - TASE-N

SP 1 - PAGE N
PC 103 JH1

DC - LOS UH
FC - CBL-FBI

FS - CPI;EPI
IS - U21L21"

IC - H01L21/306

IN - TAO H; TSAI

MC - L04-C18

- U11-C07 U11-F01B1

PA - (TASE-N) TAIWAN SEMICONDUCTOR MFG CO LTD

PN - TW434734 A 20010516 DW200201 H01L21/306 000pp

PR - TW20000100143-20000106

XA - C2002-002088

XIC - H01I-021/306

XR - N2002-007550

AB - TW434734 NOVELTY - The present invention provides a method to control the etching parameter in-situ to determine the etching parameters for etching a wafer, wherein the surface of the wafer is covered with a screening layer which forms a main pattern transferred to the wafer by using the screening layer as the mask for etching. The characteristic of this method is: forming a featured pattern before etching, which shows the featured dimension of the main pattern; use a light source to illuminate the featured pattern to obtain the featured dimension by detecting the diffracted light; determine the etching parameters based on the featured dimension.

- (Dwg.1/1)

IW - METHOD CONTROL ETCH PARAMETER SITU ILLUMINATE PATTERN OBTAIN DIMENSION DETECT DIFFRACTED LIGHT

**IKW - METHOD CONTROL ETCH PARAMETER SITU ILLUMINATE PATTERN OBTAIN DIMENSION
DETECT DIFFRACTED LIGHT**

INW - TAO H: TSALC

INW - TAV
NC 001

NC - 001
QPP 00000 01 06

OPD - 2000-01-06
SPP - 2001-05-16

DAW - STAGE N) TAIWAN SEMICONDUCTOR MFG CO LTD

TI - The method to control the etching parameter in-situ - by illuminating the featured pattern to obtain the featured dimension by detecting the diffracted light.